

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI OSC-0.7L** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	500 mA
<b>V<sub>CB</sub></b>	40 V
<b>P<sub>DISS</sub></b>	7.0 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	25 °C/W

**PACKAGE STYLE TO-46**

DIM	MINIMUM inches/mm	MAXIMUM inches/mm
A	.100 / 2.540	
B	.028 / 0.710	.048 / 1.220
C	.035 / 0.890	.046 / 1.170
D	.209 / 5.310	.229 / 5.840
E	.178 / 4.520	.195 / 4.950
F	.065 / 1.650	.085 / 2.160
G	.500 / 12.700	
H	.012 / 0.3050	.019 / 0.4830

**ORDER CODE: ASI10637**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 1.0 mA			20			<b>V</b>
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 100 μA			40			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 100 μA			3.0			<b>V</b>
<b>I<sub>CBO</sub></b>	V <sub>CB</sub> = 18 V					100	<b>μA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V	I <sub>C</sub> = 100 mA		25		250	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 18 V	f = 1.0 MHz				5.0	<b>pF</b>
<b>η<sub>C</sub></b>	V <sub>CC</sub> = 18 V	P <sub>OUT</sub> = 0.7 W	f = 1.68 GHz		25		<b>%</b>
<b>f<sub>t</sub></b>	V <sub>CE</sub> = 10 V	I <sub>E</sub> = 100 mA	f = 200 MHz		2500		<b>MHz</b>
<b>P<sub>OSC</sub></b>	V <sub>CC</sub> = 18 V	I <sub>E</sub> = 150 mA	f = 1.68 GHz		700		<b>mW</b>